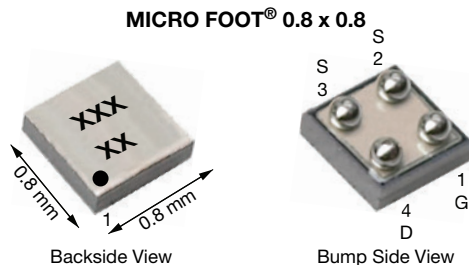


P-Channel 12 V (D-S) MOSFET


Marking code: xx = AK

xxx = Date / lot traceability code

PRODUCT SUMMARY	
V_{DS} (V)	-12
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -3.7$ V	0.080
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -2.5$ V	0.100
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.8$ V	0.190
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -1.5$ V	0.280
Q_g typ. (nC)	7
I_D (A) ^{a, e}	-2.9
Configuration	Single

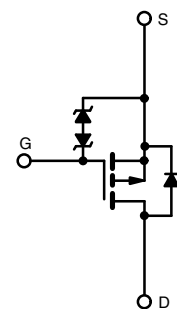
FEATURES

- TrenchFET® power MOSFET
- Small 0.8 mm x 0.8 mm outline area
- Low 0.4 mm max. profile
- Typical ESD protection 1700 V HBM
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load switches and battery switches
- High speed switching
- For smart phones, tablet PCs, and mobile computing



P-Channel MOSFET

ORDERING INFORMATION	
Package	MICRO FOOT
Lead (Pb)-free and halogen-free	Si8819EDB-T2-E1

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-source voltage		V_{DS}	-12	V
Gate-source voltage		V_{GS}	± 8	
Continuous drain current ($T_J = 150$ °C)	$T_A = 25$ °C	I_D	-2.9 ^a	A
	$T_A = 70$ °C		-2.3 ^a	
	$T_A = 25$ °C		-2.1 ^b	
	$T_A = 70$ °C		-1.7 ^b	
Pulsed drain current ($t = 100$ μ s)		I_{DM}	-15	
Continuous source-drain diode current	$T_C = 25$ °C	I_S	-0.7 ^a	W
	$T_A = 25$ °C		-0.4 ^b	
Maximum power dissipation	$T_A = 25$ °C	P_D	0.9 ^a	
	$T_A = 70$ °C		0.6 ^a	
	$T_A = 25$ °C		0.5 ^b	
	$T_A = 70$ °C		0.3 ^b	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +150	°C
Package reflow conditions ^c	VPR		260	
	IR/Convection		260	

Notes

- Surface mounted on 1" x 1" FR4 board with full copper, $t = 5$ s
- Surface mounted on 1" x 1" FR4 board with minimum copper, $t = 5$ s
- Refer to IPC/JEDEC® (J-STD-020), no manual or hand soldering
- In this document, any reference to case represents the body of the MICRO FOOT device and foot is the bump
- Based on $T_A = 25$ °C

**THERMAL RESISTANCE RATINGS**

Parameter		Symbol	Typical	Maximum	Unit
Maximum junction-to-ambient ^{a, b}	t = 5 s	R _{thJA}	105	135	°C/W
Maximum junction-to-ambient ^{c, d}	t = 5 s		200	260	

Notes

- a. Surface mounted on 1" x 1" FR4 board with full copper
b. Maximum under steady state conditions is 185 °C/W
c. Surface mounted on 1" x 1" FR4 board with minimum copper
d. Maximum under steady state conditions is 330 °C/W

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA	-12	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	I _D = -250 μA	-	-7	-	mV/°C
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J		-	2.7	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.4	-	-0.9	V
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 4.5 V	-	-	± 0.2	μA
		V _{DS} = 0 V, V _{GS} = ± 8 V	-	-	± 1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = -12 V, V _{GS} = 0 V	-	-	-1	μA
		V _{DS} = -12 V, V _{GS} = 0 V, T _J = 70 °C	-	-	-10	
On-state drain current ^a	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = -3.7 V	-5	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -3.7 V, I _D = -1.5 A	-	0.063	0.080	Ω
		V _{GS} = -2.5 V, I _D = -1.5 A	-	0.079	0.100	
		V _{GS} = -1.8 V, I _D = -1 A	-	0.118	0.190	
		V _{GS} = -1.5 V, I _D = -0.1 A	-	0.180	0.280	
Forward transconductance ^a	g _{fs}	V _{DS} = -5 V, I _D = -1.5 A	-	7	-	S
Dynamic ^b						
Input capacitance	C _{iss}	V _{DS} = -6 V, V _{GS} = 0 V, f = 1 MHz	-	620	-	pF
Output capacitance	C _{oss}		-	140	-	
Reverse transfer capacitance	C _{rss}		-	130	-	
Total gate charge	Q _g	V _{DS} = -6 V, V _{GS} = -8 V, I _D = -1.5 A	-	12	17	nC
		V _{DS} = -6 V, V _{GS} = -4.5 V, I _D = -1.5 A	-	7	8	
Gate-source charge	Q _{gs}		-	0.9	-	
Gate-drain charge	Q _{gd}		-	1.9	-	
Gate resistance	R _g	V _{GS} = -0.1 V, f = 1 MHz	-	15	-	Ω
Turn-on delay time	t _{d(on)}	V _{DD} = -6 V, R _L = 4 Ω I _D ≅ -1.5 A, V _{GEN} = -4.5 V, R _g = 1 Ω	-	17	30	ns
Rise time	t _r		-	23	45	
Turn-off delay time	t _{d(off)}		-	44	90	
Fall time	t _f		-	30	60	
Turn-on delay time	t _{d(on)}	V _{DD} = -6 V, R _L = 4 Ω I _D ≅ -1.5 A, V _{GEN} = -8 V, R _g = 1 Ω	-	7	15	
Rise time	t _r		-	16	30	
Turn-off delay time	t _{d(off)}		-	58	120	
Fall time	t _f		-	31	60	

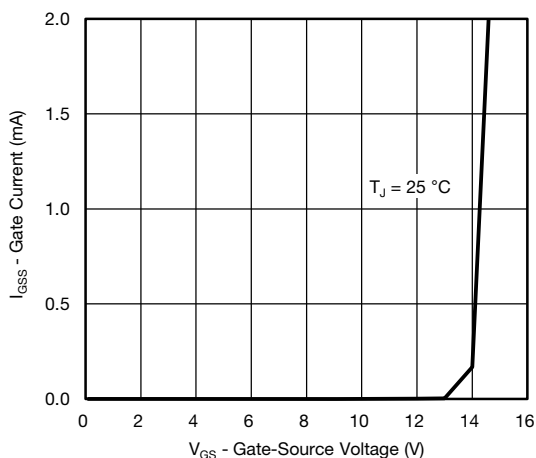
**SPECIFICATIONS** ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	$T_A = 25\text{ }^{\circ}\text{C}$	-	-	-0.7	A
Pulse diode forward current	I_{SM}		-	-	-15	
Body diode voltage	V_{SD}	$I_S = -1.5\text{ A}$, $V_{GS} = 0\text{ V}$	-	-0.82	-1.2	V
Body diode reverse recovery time	t_{rr}	$I_F = -1.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$	-	47	100	ns
Body diode reverse recovery charge	Q_{rr}		-	26	55	nC
Reverse recovery fall time	t_a		-	16	-	ns
Reverse recovery rise time	t_b		-	31	-	

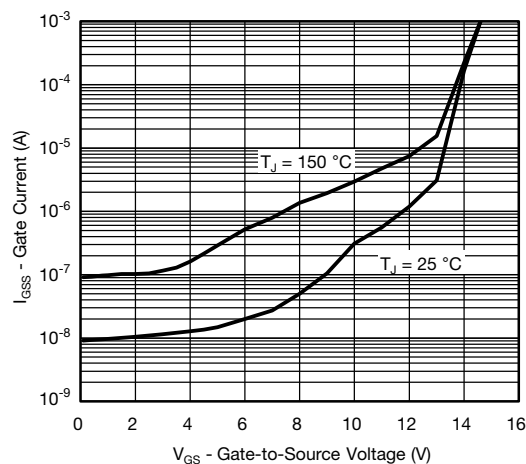
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($25\text{ }^{\circ}\text{C}$, unless otherwise noted)

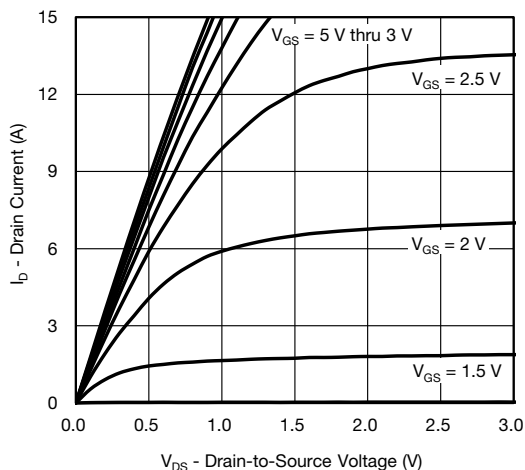
Gate Current vs. Gate-Source Voltage



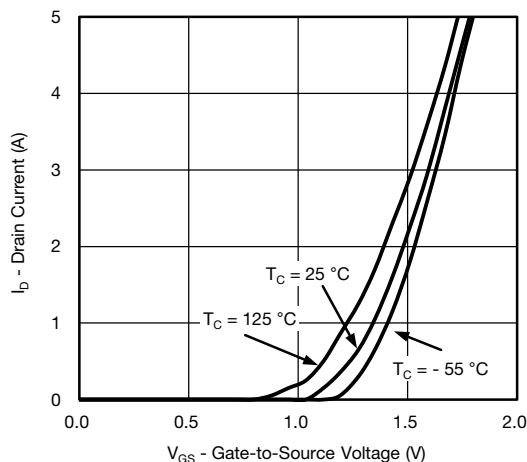
Gate Current vs. Gate-Source Voltage



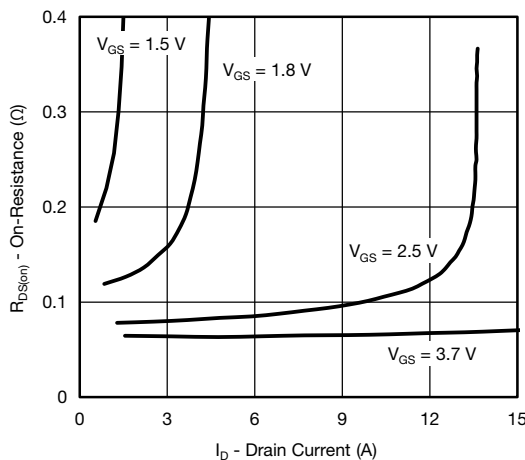
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



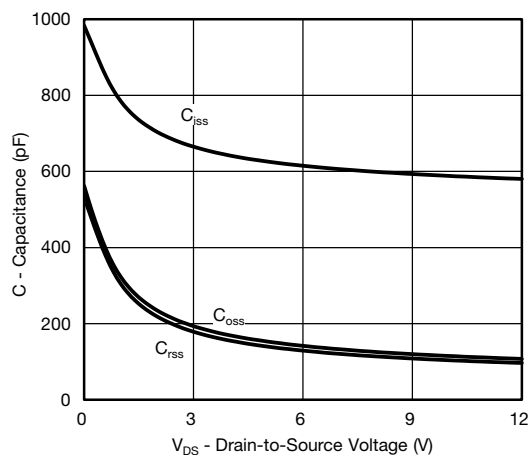
Output Characteristics



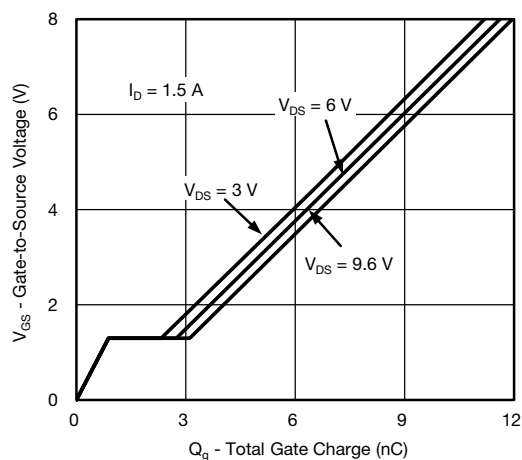
Transfer Characteristics



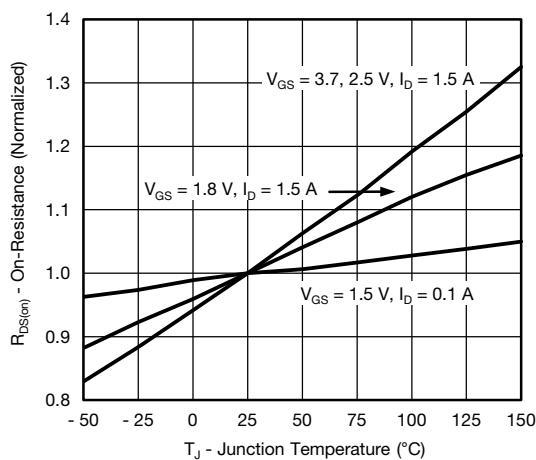
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



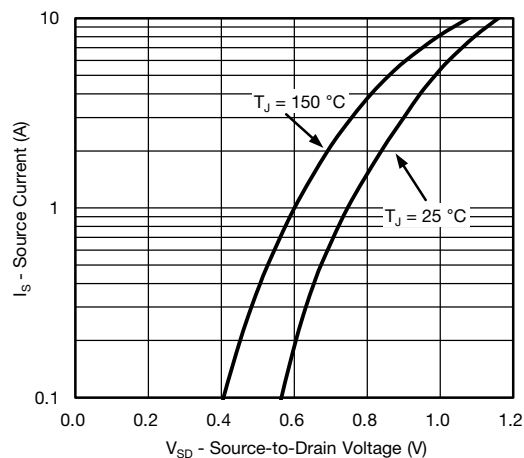
Gate Charge



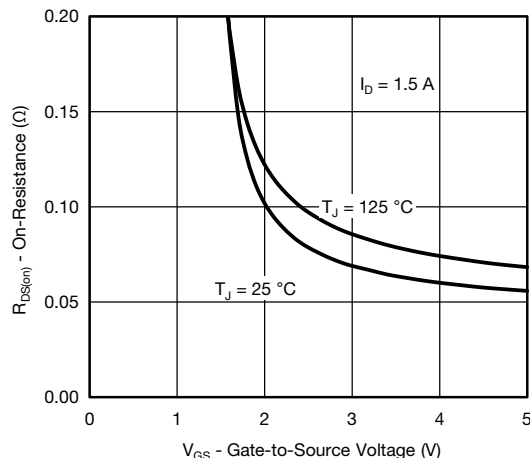
On-Resistance vs. Junction Temperature



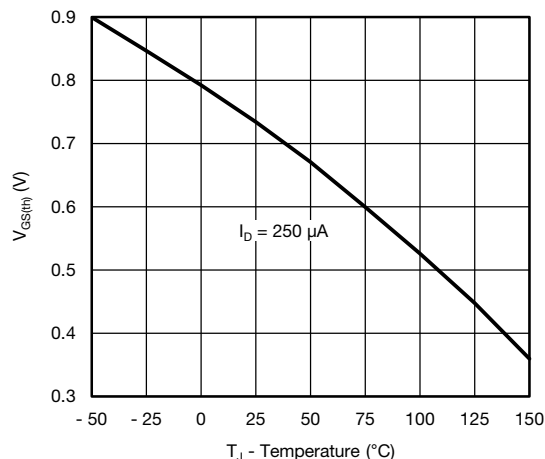
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



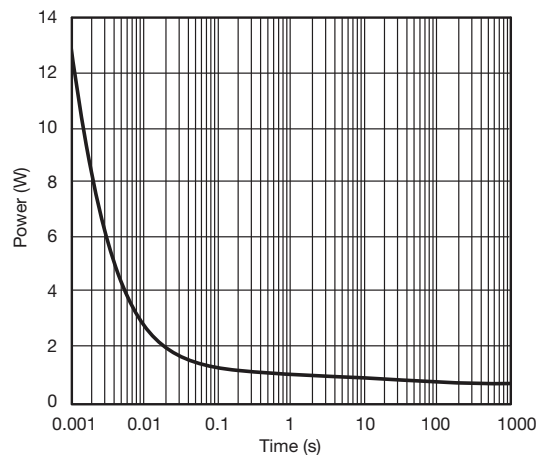
Source-Drain Diode Forward Voltage



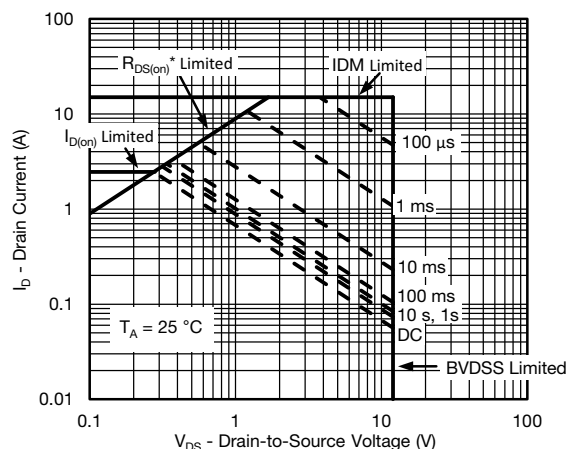
On-Resistance vs. Gate-to-Source Voltage



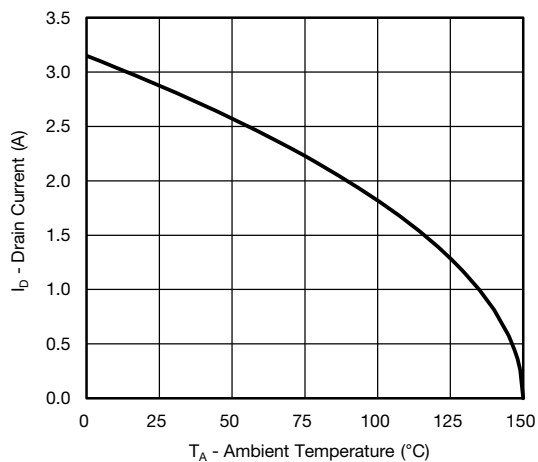
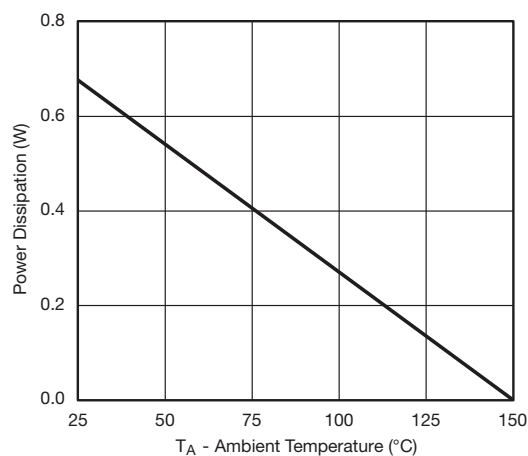
Threshold Voltage



Single Pulse Power, Junction-to-Ambient



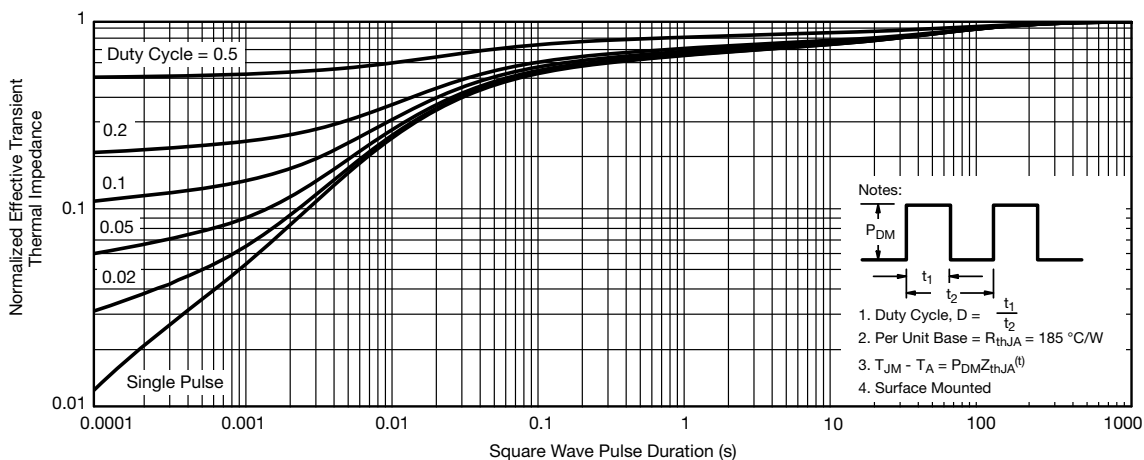
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS(25 °C, unless otherwise noted)

Current Derating ^a

Power Derating
Note

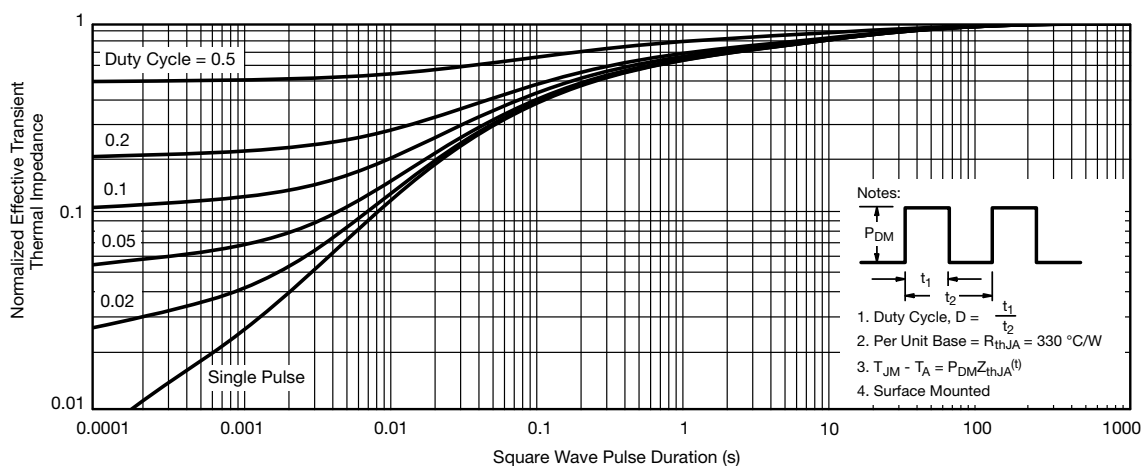
- When mounted on 1" x 1" FR4 with full copper, $t = 5$ s
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient (On 1" x 1" FR4 Board with Maximum Copper)

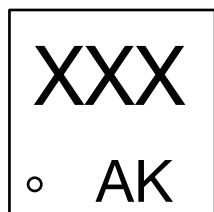


Normalized Thermal Transient Impedance, Junction-to-Ambient (On 1" x 1" FR4 Board with Minimum Copper)

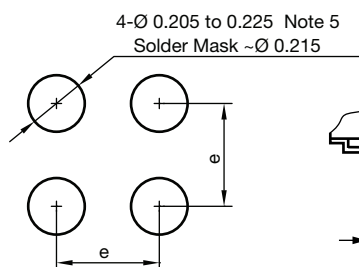
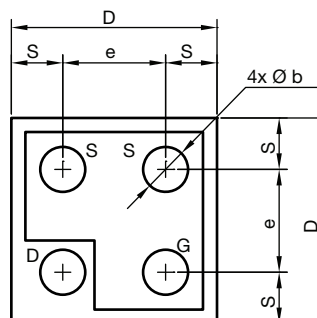
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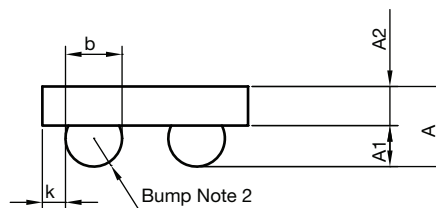
MICRO FOOT®: 4-Bump (0.8 mm x 0.8 mm, 0.4 mm Pitch)



Mark on Backside of die



Note 4



Notes

- (1) Laser mark on the backside surface of die
- (2) Bumps are 95.5 % Sn,3.8 % Ag,0.7 % Cu
- (3) "i" is the location of pin 1
- (4) "b1" is the diameter of the solderable substrate surface, defined by an opening in the solder resist layer solder mask defined.
- (5) Non-solder mask defined copper landing pad.

DIM.	MILLIMETERS ^a			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.328	0.365	0.402	0.0129	0.0144	0.0158
A1	0.136	0.160	0.184	0.0053	0.0062	0.0072
A2	0.192	0.205	0.218	0.0076	0.0081	0.0086
b	0.200	0.220	0.240	0.0078	0.0086	0.0094
b1	0.175			0.0068		
e	0.400			0.0157		
S	0.160	0.180	0.200	0.0062	0.0070	0.0078
D	0.720	0.760	0.800	0.0283	0.0299	0.0314
K	0.040	0.070	0.100	0.0015	0.0027	0.0039

Note

- a. Use millimeters as the primary measurement.

ECN: T15-0053-Rev. A, 16-Feb-15
DWG: 6033



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